

Characterization and operation of ATLASPix3

Mingjie Feng

fengmj@ihep.ac.cn

on behalf of the CEPC silicon tracker team

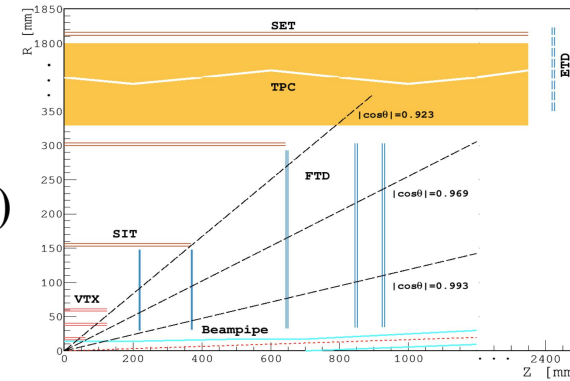
The 2022 International Workshop on the High Energy Circular Electron Positron Collider,
24-28, October, 2022



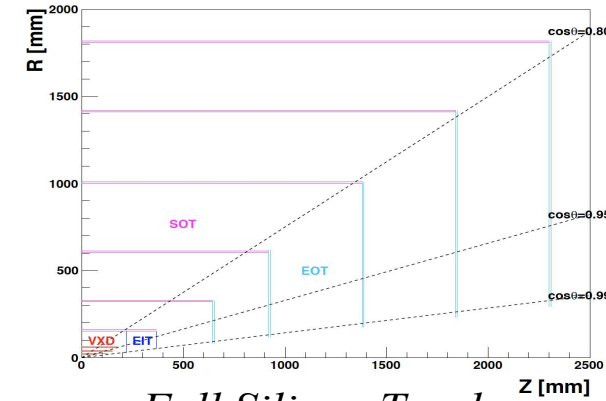
To address the physics requirements of the CEPC, a baseline and two alternative tracker designs are being considered

□ Baseline Tracker Design

- Vertex detector (VXD) with six layers
- Time Projection Chamber (TPC)
- Two inner and one outer barrel layers (**SIT** and **SET**)
- Five disks in forward region (**FTD**)



Baseline Design (TPC/Si)



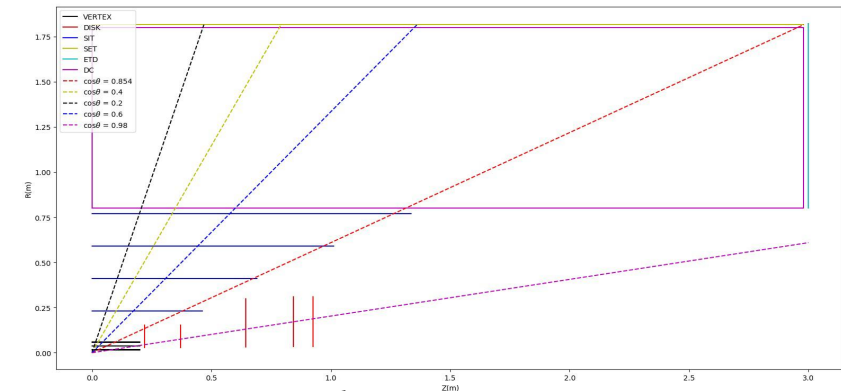
Full Silicon Tracker

□ Full Silicon Tracker Design

- Vertex detector (VXD) with six layers
- Silicon Tracker (**SOT**, **EIT** and **EOT**)

□ Fourth Design Concept

- Similar but not identical VXD with five layers
- Drift Chamber (DC)
- Outer **silicon wrapper**



Fourth Design Concept

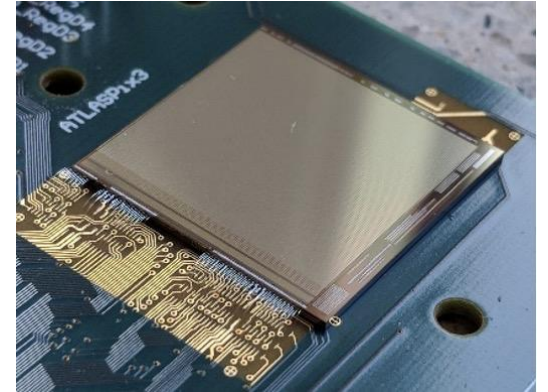
- All of them use large area silicon (Over 70m² for silicon + TPC/DC designs, about 140m² for full silicon design)
- HVCMOS technology is an economical and effective candidate!



□ ATLASPix3

The High-Voltage CMOS pixel sensor ATLASPix3 designed by KIT, and have two versions(ATLASPix3.0 and ATLASPix3.1) now

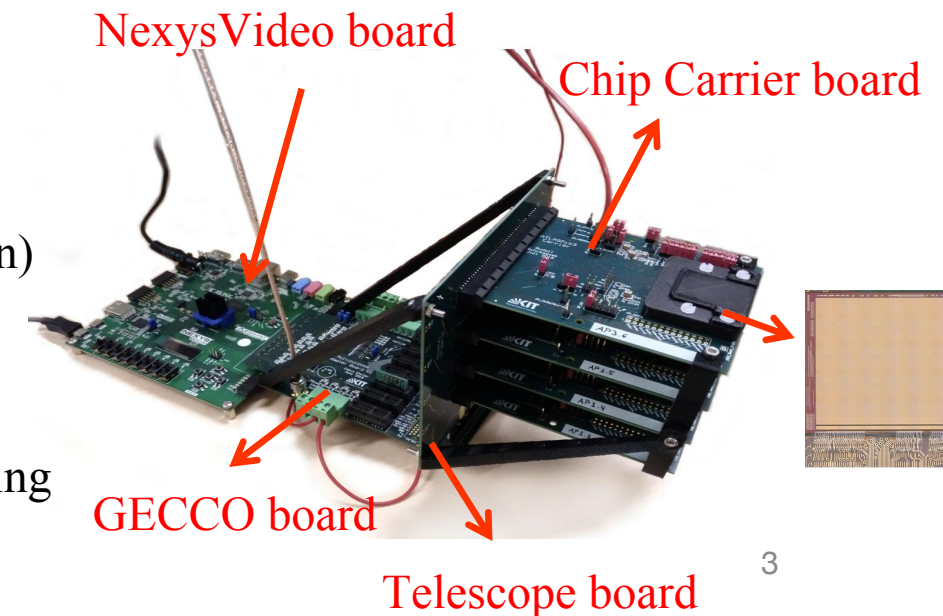
- Pixel size: $50 \times 150 \mu\text{m}^2$ (or smaller)
- 132 columns \times 372 rows (reticle size $20.2 \times 21 \text{ mm}^2$)
- Pixels contain amplifiers and comparator with threshold tune circuit
- Data output: triggerless(1.6 Gbit/s 8b/10b) /triggered(1.28 Gbit/s 64b/66b)
- 25ns timing compliant
- TSI 180 nm process on 200 Ωcm substrate



□ Readout using GEneric Configuration and COntrol System (GECCO)

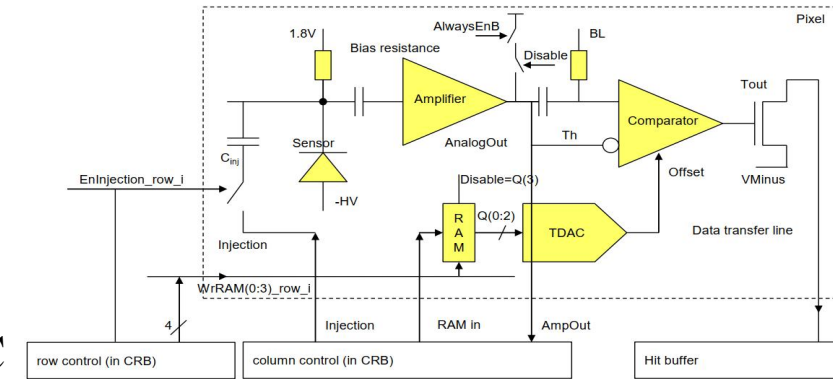
GECCO can be used with a single board or 4 boards (telescope configuration)

- Telescope module
 - One GECCO board can readout four sensors
 - KIT produced telescope cards carrying 4 sensors with $\sim 2.5 \text{ cm}$ spacing

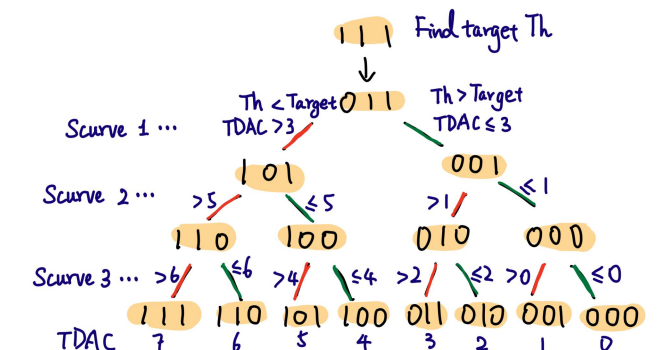
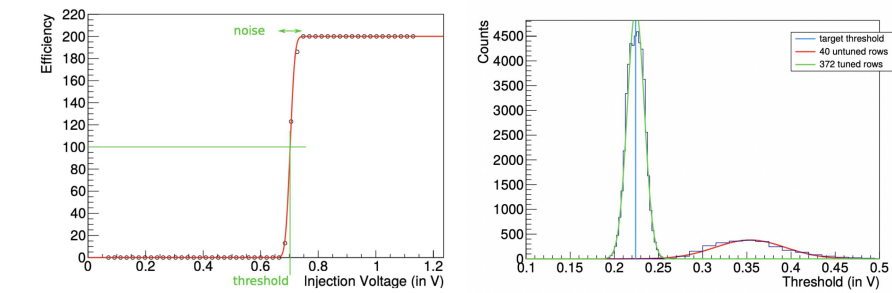




- To equalise the detection thresholds of the pixels
- Done by the in-pixel tuning circuits by varying the TDAC(tuning DAC) value
 - Each pixel contains a 3 bit TDAC and a disable bit
 - The correlation between TDAC and the threshold is linear
 - The parameter VNDAC adjusts the amount of current drained by the TDAC

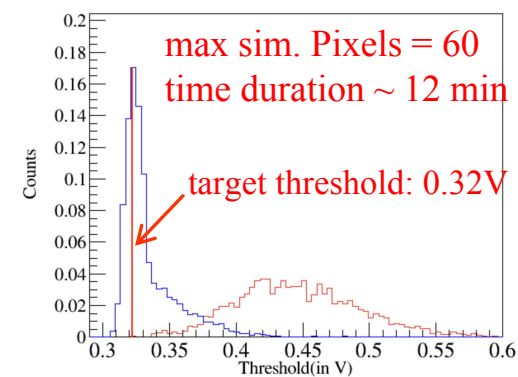
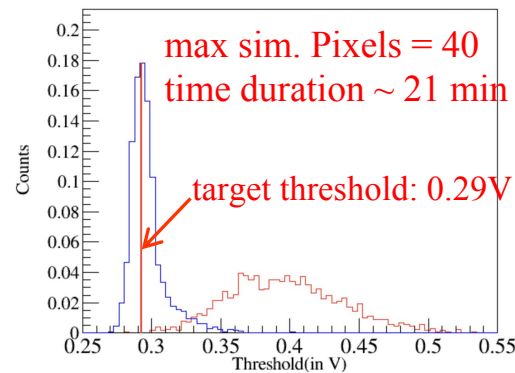
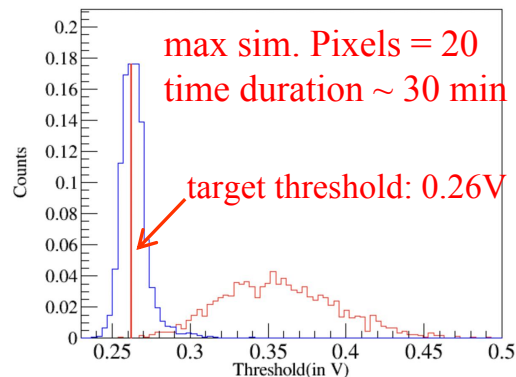


- Steps
 - Configure injection and measure scurves (once for 20 pixels)
 - Configure injection to activate pixels
 - Measure scurves for all activated pixels of the chip at the same time
 - Get target threshold
 - Target thresholds are $\mu + 3\sigma$ of untuned distribution
 - Fit scurve to get the threshold
 - Determine the best TDAC value for each pixel through a binary search





- ❑ Trimming the whole chip took a lot of time
 - 7.5 hours when max simultaneous pixels = 20 and target threshold at 1% of untuned distribution
- ❑ Time duration of each process
 - Configure injection (2ms for one time) and fit scurve (1ms for one scurve) are fast
 - Measure scurves (2s for one time) took a lot of time
- ❑ Approaches of optimization
 - Increase the number of the max simultaneous pixels
(Caveat, the signal size of the charge injection is affected when increase the number of pixels measuring at once)
 - Reduce the number of pixels with TDAC = 7 (0) through setting a lower (higher) target threshold
 - Add a mode to customize the target threshold
- ❑ 5.5 hours when max simultaneous pixels = 22 and target threshold at 0.1% of untuned distribution
- ❑ Subset: conducted for 3600 pixels:



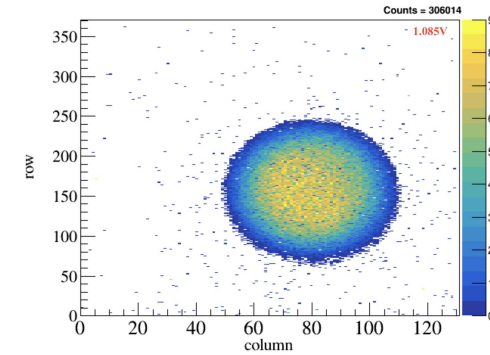


❑ Radioactive Source Test: Fe55 (5.9keV EC)

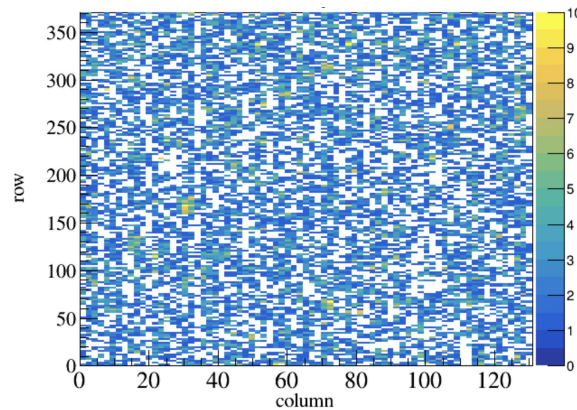
- Use single chip module
- To calibrate the Threshold with Energy
- Tape the source at the back side of the chip (with collimation)

❑ Cosmic Ray Test

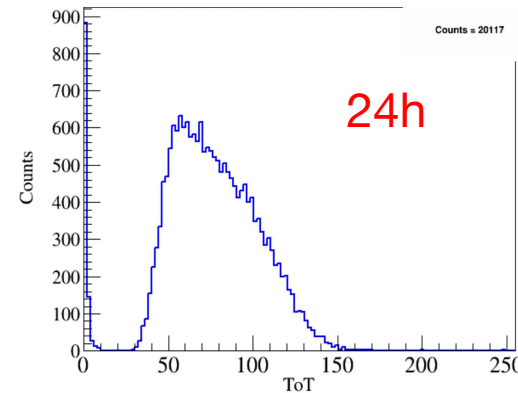
- Use telescope module
 - ATLASPix3.1 for 24 hours



Hit map



Hit map



ToT histogram